

# Product Specifications

PART NO.:

**VL41A4G63B-C3SA**
**REV: 1.0**

## General Information

### 32GB 4Gx72 DDR4 SDRAM ECC UNBUFFERED SODIMM 260-PIN

## Description

The VL41A4G63B is a 4Gx72 DDR4 SDRAM high density SODIMM. This dual rank memory module consists of eighteen CMOS 2Gx8 bits with 16 internal banks DDR4 Synchronous DRAMs in BGA packages, and a 4K EEPROM with thermal sensor in an 8-pin MLF package. This module is a 260-pin small out-line dual in-line memory module and is intended for mounting into an edge connector socket. Decoupling capacitors are mounted on the printed circuit board for each DDR4 SDRAM.

## Features

- 260-pin, small out-line dual in-line memory module (SODIMM)
- Supports ECC error detection and correction
- Fast data transfer rate: 3200MT/s
- VDD = VDDQ = 1.2V +/-0.060V
- VPP = 2.5V (2.375 min, 2.75 max)
- VDDSPD = 2.5V or 3.3V +/-10%
- 16 internal banks; 4 groups of 4 banks each
- Nominal and dynamic on-die termination (ODT)
- Low-power auto self refresh
- Programmable CAS# latency: 22 (DDR4-3200)
- Programmable burst length (8)
- Asynchronous reset
- On-die VREFDQ generation and calibration
- Fly-by topology
- On board terminated command, address, and control bus
- Serial presence detect (SPD) EEPROM with thermal sensor
- Thermal sensor range: -40°C to +125°C (Max +/-3% accuracy)
- Lead-free, RoHS compliant
- JEDEC pinout
- Gold edge contacts
- PCB: Height 30.00mm (1.181”), double sided component
- Operating temperature (TOPER)<sup>1</sup>: - Commercial (0°C to 95°C)  
- Industrial (-40°C to +95°C)

Notes: (1) Double refresh rate is required when 85°C < TOPER <= 95°C.  
TOPER is DRAM case temperature.

## Pin Description

Pin Name	Function
A0~A16	Row Address Inputs
A0~A9	Column Address Inputs
A10/AP	Address Input/ Autoprecharge
A12/BC#	Address Input/ Burst Chop
ACT#	Activate input
RAS#/A16	Row Address Strokes/ Address Input
CAS#/A15	Column Address Strokes/ Address Input
WE#/A14	Write Enable/Address Input
BA0~BA1	Bank Address Inputs
BG0~BG1	Bank group address inputs
DQ0~DQ63	Data Input/Output
DQS0~DQS8	Data Strokes
DQS0#~DQS8#	Data Strokes Complement
DM0#~DM8#	Data Mask Input
CB0~CB7	Data Check Bits I/O
PARITY	Parity Input
ALERT#	Alert output
CK0, CK0# CK1, CK1#	Clock Inputs
ODT0, ODT1	On-die Termination Controls
CKE0, CKE1	Clock Enables
CS0#, CS1#	Chip Selects
RESET#	Register and SDRAM Control
VDD	Voltage Supply
VPP	DRAM Activating Voltage Supply
VSS	Ground
SA0~SA2	SPD Address
SDA	SPD Data Input/Output
SCL	SPD Clock Input
EVENT#	Temperature Event Output
VREFCA	Reference Voltage for CA
VDDSPD	SPD Voltage Supply
VTT	Termination Voltage
NC	No Connect

## Order Information:

**VL41A4G63B - C3 S A - X**
OPERATING TEMPERATURE

 None: Commercial  
 S1: Industrial screening

DRAM DIE: A

DRAM MANUFACTURER  
 S - SAMSUNG

MODULE SPEED  
 C3: DDR4-3200 @ CL22

VL: Lead-free/RoHS

DRAM component: K4AAG085WA-BCWE

# Product Specifications

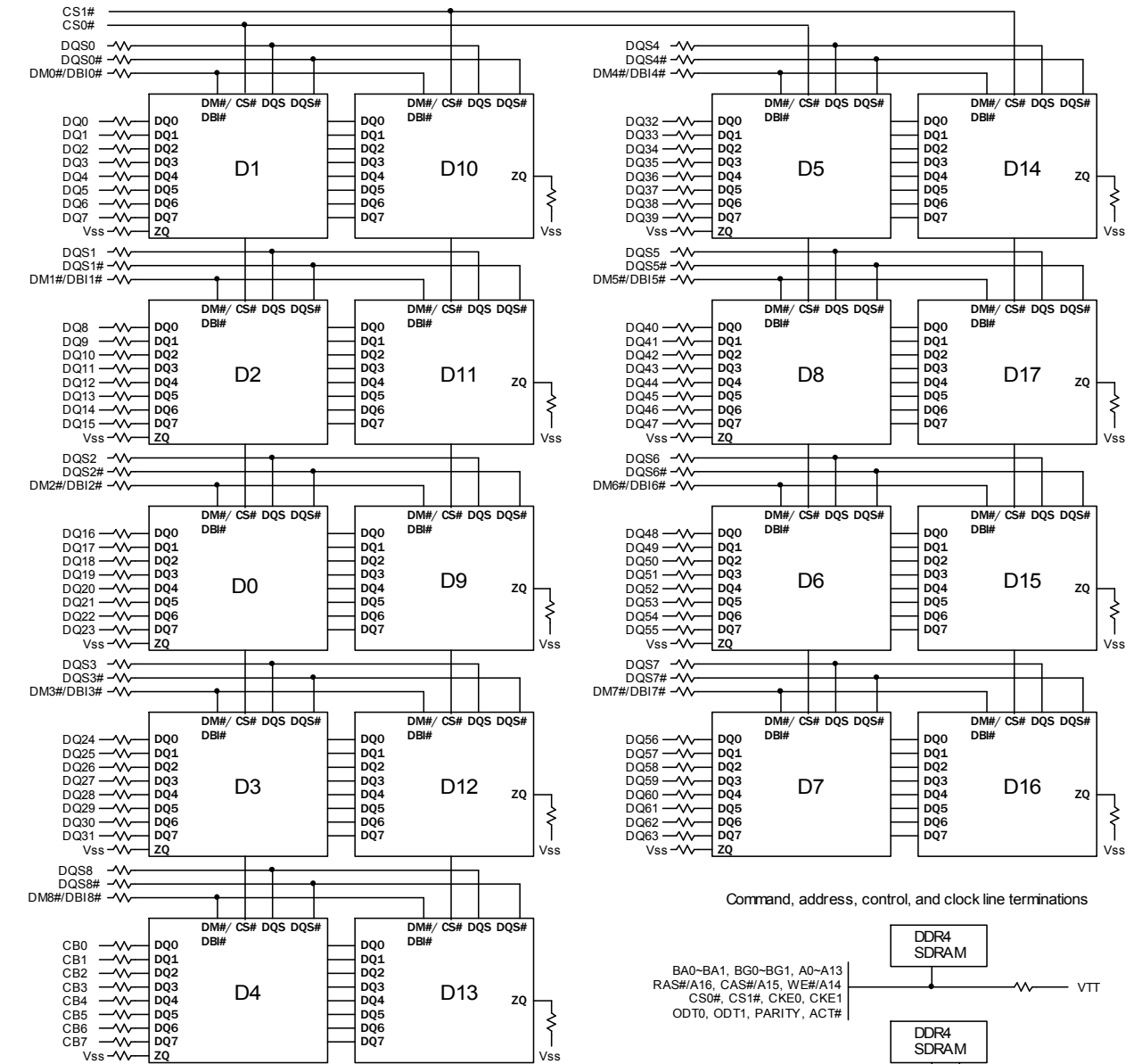
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## Pin Configuration

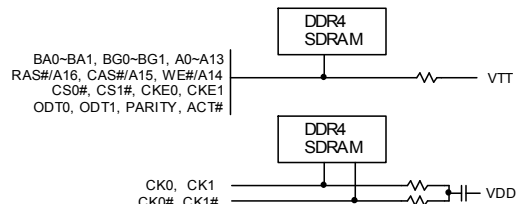
260-PIN DDR4 SODIMM FRONT SIDE								260-PIN DDR4 SODIMM BACK SIDE							
Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
1	VSS	67	DQ29	133	A1	195	DQ40	2	VSS	68	VSS	134	EVENT#	196	VSS
3	DQ5	69	VSS	135	VDD	197	VSS	4	DQ4	70	DQ24	136	VDD	198	DQS5#
5	VSS	71	DQ25	137	CK0	199	DM5#/ DBI5#	6	VSS	72	VSS	138	CK1	200	DQS5
7	DQ1	73	VSS	139	CK0#	201	VSS	8	DQ0	74	DQS3#	140	CK1#	202	VSS
9	VSS	75	DM3#/ DBI3#	141	VDD	203	DQ46	10	VSS	76	DQS3	142	VDD	204	DQ47
11	DQS0#	77	VSS	143	PARITY	205	VSS	12	DM0#/ DBI0#	78	VSS	144	A0	206	VSS
13	DQS0	79	DQ30	KEY		207	DQ42	14	VSS	80	DQ31	KEY		208	DQ43
15	VSS	81	VSS			209	VSS	16	DQ6	82	VSS			210	VSS
17	DQ7	83	DQ26	145	BA1	211	DQ52	18	VSS	84	DQ27	146	A10/AP	212	DQ53
19	VSS	85	VSS	147	VDD	213	VSS	20	DQ2	86	VSS	148	VDD	214	VSS
21	DQ3	87	CB5	149	CS0#	215	DQ49	22	VSS	88	CB4	150	BA0	216	DQ48
23	VSS	89	VSS	151	A14/WE#	217	VSS	24	DQ12	90	VSS	152	A16/RAS#	218	VSS
25	DQ13	91	CB1	153	VDD	219	DQS6#	26	VSS	92	CB0	154	VDD	220	DM6#/ DBI6#
27	VSS	93	VSS	155	ODT0	221	DQS6	28	DQ8	94	VSS	156	A15/CAS#	222	VSS
29	DQ9	95	DQS8#	157	CS1#	223	VSS	30	VSS	96	DM8#/ DBI8#	158	A13	224	DQ54
31	VSS	97	DQS8	159	VDD	225	DQ55	32	DQS1#	98	VSS	160	VDD	226	VSS
33	DM1#/ DBI1#	99	VSS	161	ODT1	227	VSS	34	DQS1	100	CB6	162	NC, C0, CS2#*	228	DQ50
35	VSS	101	CB2	163	VDD	229	DQ51	36	VSS	102	VSS	164	VREFCA	230	VSS
37	DQ15	103	VSS	165	NC, C1, CS3#*	231	VSS	38	DQ14	104	CB7	166	SA2	232	DQ60
39	VSS	105	CB3	167	VSS	233	DQ61	40	VSS	106	VSS	168	VSS	234	VSS
41	DQ10	107	VSS	169	DQ37	235	VSS	42	DQ11	108	RESET#	170	DQ36	236	DQ57
43	VSS	109	CKE0	171	VSS	237	DQ56	44	VSS	110	CKE1	172	VSS	238	VSS
45	DQ21	111	VDD	173	DQ33	239	VSS	46	DQ20	112	VDD	174	DQ32	240	DQS7#
47	VSS	113	BG1	175	VSS	241	DM7#/ DBI7#	48	VSS	114	ACT#	176	VSS	242	DQS7
49	DQ17	115	BG0	177	DQS4#	243	VSS	50	DQ16	116	ALERT#	178	DM4#/ DBI4#	244	VSS
51	VSS	117	VDD	179	DQS4	245	DQ62	52	VSS	118	VDD	180	VSS	246	DQ63
53	DQS2#	119	A12	181	VSS	247	VSS	54	DM2#/ DBI2#	120	A11	182	DQ39	248	VSS
55	DQS2	121	A9	183	DQ38	249	DQ58	56	VSS	122	A7	184	VSS	250	DQ59
57	VSS	123	VDD	185	VSS	251	VSS	58	DQ22	124	VDD	186	DQ35	252	VSS
59	DQ23	125	A8	187	DQ34	253	SCL	60	VSS	126	A5	188	VSS	254	SDA
61	VSS	127	A6	189	VSS	255	VDDSPD	62	DQ18	128	A4	190	DQ45	256	SA0
63	DQ19	129	VDD	191	DQ44	257	VPP	64	VSS	130	VDD	192	VSS	258	VTT
65	VSS	131	A3	193	VSS	259	VPP	66	DQ28	132	A2	194	DQ41	260	SA1

\*: These pins are not used in this module.

## Function Block Diagram



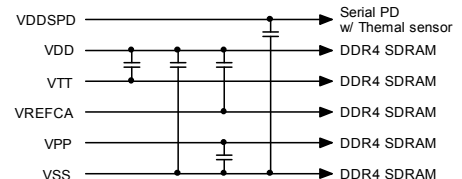
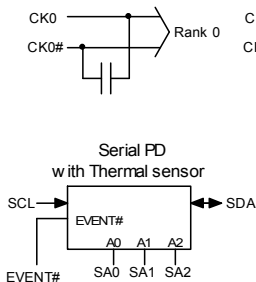
Command, address, control, and clock line terminations



- BA0-BA1 → BA0-BA1: DDR4 SDRAM
- BG0-BG1 → BG0-BG1: DDR4 SDRAM
- ACT# → ACT#: DDR4 SDRAM
- A0-A13 → A0-A13: DDR4 SDRAM
- RAS#/A16 → RAS#/A16: DDR4 SDRAM
- CAS#/A15 → CAS#/A15: DDR4 SDRAM
- WE#/A14 → WE#/A14: DDR4 SDRAM
- CKE0 → CKE0: DDR4 SDRAM D[8:0]
- CKE1 → CKE1: DDR4 SDRAM D[17:9]
- ODT0 → ODT0: DDR4 SDRAM D[8:0]
- ODT1 → ODT1: DDR4 SDRAM D[17:9]
- RESE# → RESE#: DDR4 SDRAM
- PARITY → PARITY: DDR4 SDRAM
- ALERT# → ALERT#: DDR4 SDRAM

**Notes:**

1. ZQ resistors are 240 ohms +/-1%



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### Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit	Notes
VDD	Voltage on VDD pin relative to VSS	-0.4	1.5	V	1
VDDQ	Voltage on VDDQ pin relative to VSS	-0.4	1.5	V	1
VPP	Voltage on VPP pin relative to VSS	-0.4	3.0	V	2
VIN, VOUT	Voltage on any pin relative to VSS	-0.4	1.5	V	
TSTG	Storage temperature	-55	100	°C	

- Notes:
- VDDQ balls on DRAM are tied to VDD.
  - VPP must be greater than or equal to VDD at all times.

### DC Operating Conditions

Symbol	Parameter	Min	Typical	Max	Unit	Notes	
VDD	VDD Supply Voltage	1.14	1.2	1.26	V	1	
VDDQ	VDDQ Supply Voltage for Input/Output	1.14	1.2	1.26	V	1	
VPP	DRAM Activating Power Supply	2.375	2.5	2.750	V	2	
VREFCA (DC)	Input reference voltage CMD/ADD bus	0.49 x VDD	0.5 x VDD	0.51 x VDD	V	3	
VTT	Termination Reference Voltage (DC) - command/address bus	0.49 x VDD - 20mV	0.5 x VDDQ	0.51 x VDD + 20mV	V	4	
IVTT	Termination reference current from VTT	-750	-	750	mA		
I <sub>l</sub>	Input leakage current; any input excluding ZQ; 0V < VIN < 1.1V	Address inputs, RAS#, CAS#, WE#, BA, BG, PARITY	-36	-	36	uA	
		CK, CK#, CS#, CKE, ODT	-18	-	18	uA	
		DM#	-4	-	4	uA	
I <sub>l</sub>	Input leakage current; ZQ	-54	-	54	uA	5	
I <sub>I/O</sub>	DQ leakage; 0V < Vin < VDD	-72	-	72	uA		
IOZpd	Output leakage current; VOUT=VDD; DQ is disabled	-	-	5	uA		
IOZpu	Output leakage current; VOUT = VSS; DQ and ODT are disabled; ODT is disabled with ODT input HIGH	-	-	50	uA		
IVREFCA	VREFCA leakage; VREFCA = VDD/2 (after DRAM is initialized)	-36	-	36	uA		

- Notes:
- VDDQ tracks with VDD; VDDQ and VDD are tied together.
  - DC bandwidth is limited to 20 MHz.
  - VREFCA must not be greater than 0.6 x VDD. When VDD is less than 500mV, VREF may be less than or equal to 300mV.
  - VTT termination voltages in excess of specification limit will adversely affect command and address signals' voltage margins, and reduce timing margins.
  - Tied to ground. Not connected to edge connector.

### Operating Temperature Condition

Symbol	Parameter	Rating	Units	Notes
TOPER	Operating temperature	Commercial	°C	1,2
		Industrial		

- Notes:
- Operating temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JEDEC JESD51-2.
  - At -40°C to +85°C, operation temperature range, all DRAM specifications will be supported. The refresh rate is required to double when 85°C < TOPER <= 95°C.

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## Speed Bins

Symbol	C3 DDR4-3200 (22-22-22) <sup>1</sup>	C2 DDR4-2933 (21-21-21) <sup>1</sup>	N8 DDR4-2666 (19-19-19) <sup>1</sup>	N7 DDR4-2400 (17-17-17) <sup>1</sup>	N6 DDR4-2133 (15-15-15) <sup>1</sup>	M4 DDR4-1866 (13-13-13) <sup>1</sup>	K2 DDR4-1600 (11-11-11) <sup>1</sup>	Unit
tCK(min)	0.625	0.682	0.75	0.833	0.938	1.071	1.25	ns
CAS Latency	22	21	19	17	15	13	11	nCK
tRCD(min)	13.75	14.32	14.25	14.16	14.06	13.92	13.75	ns
tRP(min)	13.75	14.32	14.25	14.16	14.06	13.92	13.75	ns
tRAS(min)	32	32	32	32	33	34	35	ns
tRC(min)	45.75	46.32	46.25	46.16	47.06	47.92	48.75	ns

Note: 1. Speed bin is in order of CL-tRCD-tRP

## Command/Address Input Levels

Symbol	Parameter	N6/N7 DDR4-2133/2400		N8/C2/C3 DDR4-2666/2933/3200		Unit	Note
		Min	Max	Min	Max		
VIH(DC)	DC Input High (Logic 1) Voltage	VREF + 0.075	VDD	VREF + 0.065	VDD	V	1,2,3
VIL(DC)	DC Input Low (Logic 0) Voltage	VSS	VREF - 0.075	VSS	VREF - 0.065	V	1,2
VIH(AC)	AC Input High (Logic 1) Voltage	VREF + 0.100	VDD	VREF + 0.090	VDD	V	1,2
VIL(AC)	AC Input Low (Logic 0) Voltage	VSS	VREF - 0.100	VSS	VREF - 0.090	V	1,2,3

- Notes:
- For input except RESET#. VREF = VREFCA(DC).
  - VREF = VREFCA(DC).
  - Input signal must meet VIL/VIH(AC) to meet tIS/tIH timings.

## AC & DC Output Levels

Symbol	Parameter	Value	Unit	Note
VOH(DC)	DC output high measurement level (for IV curve linearity)	1.1 x VDDQ	V	
VOM(DC)	DC output mid measurement level (for IV curve linearity)	0.8 x VDDQ	V	
VOL(DC)	DC output low measurement level (for IV curve linearity)	0.5 x VDDQ	V	
VOH(AC)	AC output high measurement level (for output SR)	(0.7 + 0.15) x VDDQ	V	1
VOL(AC)	AC output low measurement level (for output SR)	(0.7 - 0.15) x VDDQ	V	1
VOHdiff(AC)	AC differential output high measurement level (for output SR)	+0.3 x VDDQ	V	2
VOLdiff(AC)	AC differential output low measurement level (for output SR)	-0.3 x VDDQ	V	2

- Notes:
- The swing of  $\pm 0.15 \times VDDQ$  is based on approximately 50% of the static single-ended output peak-to-peak swing with a driver impedance of RZQ/7 $\Omega$  and an effective test load of 50 $\Omega$  to VTT = VDDQ.
  - The swing of  $\pm 0.3 \times VDDQ$  is based on approximately 50% of the static single-ended output peak-to-peak swing with a driver impedance of RZQ/7 $\Omega$  and an effective test load of 50 $\Omega$  to VTT = VDDQ.

## Input/Output Capacitance

TA=25°C, f=100MHz

Parameter	Symbol	C3 (DDR4-3200)		Unit
		Min	Max	
Input capacitance (BA0~BA1, BG0~BG1, A0~A13, RAS#/A16, CAS#/A15, WE#/A14, ACT#)	CIN1	7.6	13.9	pF
Input capacitance (CKE0, CKE1), (ODT0, ODT1), (CS0#, CS1#)	CIN2	5.8	9.0	pF
Input capacitance (CK0, CK1#, CK1#)	CIN3	5.8	10.3	pF
Input/Output capacitance (DQ, DQS, DQS#, DM#, CB)	CIO	5.1	6.0	pF

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### IDD & IPP Specifications

Parameter	Symbol	C3 (DDR4-3200)	Unit
One bank ACTIVATE-PRECHARGE current	IDD0	693	mA
One bank ACTIVATE-PRECHARGE, word line boost, IPP current	IPP0	72	mA
One bank ACTIVATE-READ-PRECHARGE current	IDD1	738	mA
Precharge standby current	IDD2N	540	mA
Precharge standby ODT current	IDD2NT	558	mA
Precharge power-down current	IDD2P	396	mA
Precharge quiet standby current	IDD2Q	504	mA
Active standby current	IDD3N	738	mA
Active standby IPP current	IPP3N	72	mA
Active power-down current	IDD3P	558	mA
Burst read current	IDD4R	1422	mA
Burst write current	IDD4W	1278	mA
Burst refresh current (1 x REF)	IDD5B	3375	mA
Burst refresh IPP current (1 x REF)	IPP5B	441	mA
Self refresh current: Normal temperature range (0°C to +85°C)	IDD6N	774	mA
Self refresh current: Extended temperature range (0°C to +95°C)	IDD6E	1206	mA
Self refresh current: Reduced temperature range (0°C to +45°C)	IDD6R	558	mA
Auto self refresh current	IDD6A	774	mA
Bank interleave read current	IDD7	1998	mA
Bank interleave read IPP current	IPP7	162	mA
Maximum power-down current	IDD8	396	mA

Note:  
 IDD specification is based on Samsung 16Gb A-die components.  
 (\*) Use tRFC1 550ns setting.

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## AC TIMING PARAMETERS & SPECIFICATIONS

Speed		C3 DDR4-3200		C2 DDR4-2933		N8 DDR4-2666		N7 DDR4-2400		N6 DDR4-2133		M4 DDR4-1866		K2 DDR4-1600		Units
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
<b>Clock Timing</b>																
Minimum Clock Cycle Time (DLL off mode)	tCK (DLL_OFF)	8	20	8	20	8	20	8	20	8	20	8	20	8	20	ns
Average Clock Period	tCK(avg)	0.625	<0.682	0.682	<0.750	0.750	<0.833	0.833	<0.937	0.937	<1.071	1.071	<1.25	1.25	<1.5	ns
Average high pulse width	tCH(avg)	0.48	0.52	0.48	0.52	0.48	0.52	0.48	0.52	0.48	0.52	0.48	0.52	0.48	0.52	tCK(avg)
Average low pulse width	tCL(avg)	0.48	0.52	0.48	0.52	0.48	0.52	0.48	0.52	0.48	0.52	0.48	0.52	0.48	0.52	tCK(avg)
Absolute Clock Period	tCK(abs)	MIN : tCK(avg)min + tJIT(per)min_tot MAX : tCK(avg)max + tJIT(per)max_tot														tCK(avg)
Absolute clock HIGH pulse width	tCH(abs)	0.45	-	0.45	-	0.45	-	0.45	-	0.45	-	0.45	-	0.45	-	tCK(avg)
Absolute clock LOW pulse width	tCL(abs)	0.45	-	0.45	-	0.45	-	0.45	-	0.45	-	0.45	-	0.45	-	tCK(avg)
Clock Period Jitter- total	tJIT(per)_tot	-32	32	-34	34	-38	38	-42	42	-47	47	-54	54	-63	63	ps
Clock Period Jitter- deterministic	tJIT(per)_dj	-16	16	-17	17	-19	19	-21	21	-23	23	-27	27	-31	31	ps
Clock Period Jitter during DLL locking period	tJIT(per)_lck	-25	25	-27	27	-30	30	-33	33	-38	38	-43	43	-50	50	ps
Cycle to Cycle Period Jitter	tJIT(cc)	-	62	-	68	-	75	-	83	-	94	-	107	-	125	ps
Cycle to Cycle Period Jitter during DLL locking period	tJIT(cc)_lck	-	50	-	55	-	60	-	67	-	75	-	86	-	100	ps
Cumulative error across 2 cycles	tERR(2per)	-46	46	-50	50	-55	55	-61	61	-69	69	-79	79	-92	92	ps
Cumulative error across 3 cycles	tERR(3per)	-55	55	-60	60	-66	66	-73	73	-82	82	-94	94	-109	109	ps
Cumulative error across 4 cycles	tERR(4per)	-61	61	-66	66	-73	73	-81	81	-91	91	-104	104	-121	121	ps
Cumulative error across 5 cycles	tERR(5per)	-65	65	-71	71	-78	78	-87	87	-98	98	-112	112	-131	131	ps
Cumulative error across 6 cycles	tERR(6per)	-69	69	-75	75	-83	83	-92	92	-104	104	-119	119	-139	139	ps
Cumulative error across 7 cycles	tERR(7per)	-73	73	-79	79	-87	87	-97	97	-109	109	-124	124	-145	145	ps
Cumulative error across 8 cycles	tERR(8per)	-76	76	-83	83	-91	91	-101	101	-113	113	-129	129	-151	151	ps
Cumulative error across 9 cycles	tERR(9per)	-78	78	-85	85	-94	94	-104	104	-117	117	-134	134	-156	156	ps
Cumulative error across 10 cycles	tERR(10per)	-80	80	-88	88	-96	96	-107	107	-120	120	-137	137	-160	160	ps
Cumulative error across 11 cycles	tERR(11per)	-83	83	-90	90	-99	99	-110	110	-123	123	-141	141	-164	164	ps
Cumulative error across 12 cycles	tERR(12per)	-84	84	-92	92	-101	101	-112	112	-126	126	-144	144	-168	168	ps
Cumulative error across 13 cycles	tERR(13per)	-86	86	-93	93	-103	103	-114	114	-129	129	-147	147	-172	172	ps
Cumulative error across 14 cycles	tERR(14per)	-87	87	-95	95	-104	104	-116	116	-131	131	-150	150	-175	175	ps
Cumulative error across 15 cycles	tERR(15per)	-89	89	-97	97	-106	106	-118	118	-133	133	-152	152	-178	178	ps
Cumulative error across 16 cycles	tERR(16per)	-90	90	-98	98	-108	108	-120	120	-135	135	-155	155	-180	189	ps
Cumulative error across 17 cycles	tERR(17per)	-92	92	-100	100	-110	110	-122	122	-137	137	-157	157	-183	183	ps
Cumulative error across 18 cycles	tERR(18per)	-93	93	-101	101	-112	112	-124	124	-139	139	-159	159	-185	185	ps
Cumulative error across n = 13, 14 . . . 49, 50 cycles	tERR(nper)	MIN : tERR(nper)min = ((1 + 0.68ln(n)) * tJIT(per)_total min) MAX : tERR(nper)max = ((1 + 0.68ln(n)) * tJIT(per)_total max)														ps
Command and Address setup time to CK, CK# referenced to Vih(ac) / Vil(ac) levels	tIS(base)	40	-	48	-	55	-	62	-	80	-	100	-	115	-	ps
Command and Address setup time to CK, CK# referenced to Vref levels	tIS(Vref)	130	-	138	-	145	-	162	-	180	-	200	-	215	-	ps
Command and Address hold time to CK, CK# referenced to Vih(dc) / Vil(dc) levels	tIH(base)	65	-	73	-	80	-	87	-	105	-	125	-	140	-	ps
Command and Address hold time to CK, CK# referenced to Vref levels	tIH(Vref)	130	-	138	-	145	-	162	-	180	-	200	-	215	-	ps
Control and Address Input pulse width for each input	tIPW	340	-	365	-	385	-	410	-	460	-	525	-	600	-	ps

# Product Specifications

PART NO.:

**VL41A4G63B-C3SA**
**REV: 1.0**

## AC TIMING PARAMETERS & SPECIFICATIONS

Speed		C3 DDR4-3200		C2 DDR4-2933		N8 DDR4-2666		N7 DDR4-2400		N6 DDR4-2133		M4 DDR4-1866		K2 DDR4-1600		Units
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
<b>Command and Address Timing</b>																
CAS# to CAS# command de- lay for same bank group	tCCD_L	max(5 nCK, 5 ns)	-	max(5 nCK, 5 ns)	-	max(5 nCK, 5 ns)	-	max(5 nCK, 5 ns)	-	max(5 nCK, 5.355 ns)	-	max(5 nCK, 5.355 ns)	-	max(5 nCK, 6.250 ns)	-	nCK
CAS# to CAS# command de- lay for different bank group	tCCD_S	4	-	4	-	4	-	4	-	4	-	4	-	4	-	nCK
ACTIVATE to ACTIVATE Com- mand delay to different bank group for 2KB page size	tRRD_S(2K)	Max(4nC K, 5.3ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 6ns)	-	nCK
ACTIVATE to ACTIVATE Com- mand delay to different bank group for 2KB page size	tRRD_S(1K)	Max(4nC K, 2.5ns)	-	Max(4nC K, 2.7ns)	-	Max(4nC K, 3ns)	-	Max(4nC K, 3.3ns)	-	Max(4nC K, 3.7ns)	-	Max(4nC K, 4.2ns)	-	Max(4nC K, 5ns)	-	nCK
ACTIVATE to ACTIVATE Com- mand delay to different bank group for 1/2KB page size	tRRD_S(1/2K)	Max(4nC K, 2.5ns)	-	Max(4nC K, 2.7ns)	-	Max(4nC K, 3ns)	-	Max(4nC K, 3.3ns)	-	Max(4nC K, 3.7ns)	-	Max(4nC K, 4.2ns)	-	Max(4nC K, 5ns)	-	nCK
ACTIVATE to ACTIVATE Com- mand delay to same bank group for 2KB page size	tRRD_L(2K)	Max(4nC K, 6.4ns)	-	Max(4nC K, 6.4ns)	-	Max(4nC K, 6.4ns)	-	Max(4nC K, 6.4ns)	-	Max(4nC K, 6.4ns)	-	Max(4nC K, 6.4ns)	-	Max(4nC K, 7.5ns)	-	nCK
ACTIVATE to ACTIVATE Com- mand delay to same bank group for 1KB page size	tRRD_L(1K)	Max(4nC K, 4.9ns)	-	Max(4nC K, 4.9ns)	-	Max(4nC K, 4.9ns)	-	Max(4nC K, 4.9ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 6ns)	-	nCK
ACTIVATE to ACTIVATE Com- mand delay to same bank group for 1/2KB page size	tRRD_L(1/2K)	Max(4nC K, 4.9ns)	-	Max(4nC K, 4.9ns)	-	Max(4nC K, 4.9ns)	-	Max(4nC K, 4.9ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 5.3ns)	-	Max(4nC K, 6ns)	-	nCK
Four activate window for 2KB page size	tFAW_2K	Max(28n CK, 30ns)	-	Max(28n CK, 30ns)	-	Max(28n CK, 30ns)	-	Max(28n CK, 30ns)	-	Max(28n CK, 30ns)	-	Max(28n CK, 30ns)	-	Max(28n CK, 35ns)	-	ns
Four activate window for 1KB page size	tFAW_1K	Max(20n CK, 21ns)	-	Max(20n CK, 21ns)	-	Max(20n CK, 21ns)	-	Max(20n CK, 21ns)	-	Max(20n CK, 21ns)	-	Max(20n CK, 23ns)	-	Max(20n CK, 25ns)	-	ns
Four activate window for 1/2KB page size	tFAW_1/2K	Max(16n CK, 10ns)	-	Max (16nCK, 10.875ns)	-	Max(16n CK, 12ns)	-	Max(16n CK, 13ns)	-	Max(16n CK, 15ns)	-	Max(16n CK, 17ns)	-	Max(16n CK, 20ns)	-	ns
Delay from start of internal write transaction to internal read com- mand for different bank group	tWTR_S	max (2nCK, 2.5ns)	-	Max (2nCK, 2.5ns)	-	Max (2nCK, 2.5ns)	-	Max (2nCK, 2.5ns)	-	max(2nCK, 2.5ns)	-	max(2nCK, 2.5ns)	-	max(2nCK, 2.5ns)	-	ns
Delay from start of internal write transaction to internal read com- mand for same bank group	tWTR_L	max (4nCK, 7.5 ns)	-	max (4nCK, 7.5 ns)	-	max (4nCK, 7.5 ns)	-	max (4nCK, 7.5 ns)	-	max(4nCK, 7.5 ns)	-	max(4nCK, 7.5ns)	-	max(4nCK, 7.5ns)	-	ns
Internal READ Command to PRECHARGE Command delay	tRTP	max (4nCK, 7.5 ns)	-	max (4nCK, 7.5 ns)	-	max (4nCK, 7.5 ns)	-	max (4nCK, 7.5 ns)	-	max(4nCK, 7.5ns)	-	max(4nCK, 7.5ns)	-	max(4nCK, 7.5ns)	-	ns
WRITE recovery time	tWR	15	-	15	-	15	-	15	-	15	-	15	-	15	-	ns
Write recovery time when CRC and DM are enabled	tWR_CRC_DM	tWR+max (5nCK, 3.7 5ns)	-	tWR+max (5nCK, 3.7 5ns)	-	tWR+max (5nCK, 3.7 5ns)	-	tWR+max (5nCK, 3.7 5ns)	-	tWR+max (5nCK, 3.7 5ns)	-	tWR+max (5nCK, 3.7 5ns)	-	tWR+max (4nCK, 3.7 5ns)	-	ns
Delay from start of internal write transaction to internal read com- mand for different bank group with both CRC and DM enabled	tWTR_S_C RC_DM	tWTR_S+ max (5nCK, 3.7 5ns)	-	tWTR_S+ max (5nCK, 3.7 5ns)	-	tWTR_S+ max (5nCK, 3.7 5ns)	-	tWTR_S+ max (5nCK, 3.7 5ns)	-	tWTR_S+ max (5nCK, 3.7 5ns)	-	tWTR_S+ max (5nCK, 3.7 5ns)	-	tWTR_S+ max (4nCK, 3.7 5ns)	-	ns
Delay from start of internal write transaction to internal read com- mand for same bank group with both CRC and DM enabled	tWTR_L_C RC_DM	tWTR_L+ max (5nCK, 3.7 5ns)	-	tWTR_L+ max (5nCK, 3.7 5ns)	-	tWTR_L+ max (5nCK, 3.7 5ns)	-	tWTR_L+ max (5nCK, 3.7 5ns)	-	tWTR_L+ max (5nCK, 3.7 5ns)	-	tWTR_L+ max (5nCK, 3.7 5ns)	-	tWTR_L+ max (4nCK, 3.7 5ns)	-	ns
DLL locking time	tDLLK	1024	-	1024	-	1024	-	768	-	768	-	597	-	597	-	nCK
Mode Register Set command cy- cle time	tMRD	8	-	8	-	8	-	8	-	8	-	8	-	8	-	nCK
Mode Register Set command up- date delay	tMOD	max(24n CK, 15ns)	-	max(24n CK, 15ns)	-	max(24n CK, 15ns)	-	max(24n CK, 15ns)	-	max(24n CK, 15ns)	-	max(24n CK, 15ns)	-	max(24n CK, 15ns)	-	nCK
Multi-Purpose Register Recovery Time	tMPRR	1	-	1	-	1	-	1	-	1	-	1	-	1	-	nCK
Multi Purpose Register Write Re- covery Time	tWR_MPR	tMOD (min) + AL + PL	-	tMOD (min) + AL + PL	-	tMOD (min) + AL + PL	-	tMOD (min) + AL + PL	-	tMOD (min) + AL + PL	-	tMOD (min) + AL + PL	-	tMOD (min) + AL + PL	-	ns
Auto precharge write recovery + precharge time	tDAL(min)	Programmed WR + roundup (tRP / tCK(avg))														nCK
DQ0 or DQL0 driven to 0 set-up time to first DQS rising edge	tPDA_S	0.5	-	0.5	-	0.5	-	0.5	-	0.5	-	0.5	-	0.5	-	UI
DQ0 or DQL0 driven to 0 hold time from last DQS falling edge	tPDA_H	0.5	-	0.5	-	0.5	-	0.5	-	0.5	-	0.5	-	0.5	-	UI



# Product Specifications

**PART NO.:**
**VL41A4G63B-C3SA**
**REV: 1.0**

## AC TIMING PARAMETERS & SPECIFICATIONS

Speed		C3 DDR4-3200		C2 DDR4-2933		N8 DDR4-2666		N7 DDR4-2400		N6 DDR4-2133		M4 DDR4-1866		K2 DDR4-1600		Units
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
<b>CS# to Command Address Latency</b>																
CS# to Command Address Latency	tCAL	max(3 nCK, 3.748 ns)	-	max(3 nCK, 3.748 ns)	-	max(3 nCK, 3.748 ns)	-	max(3 nCK, 3.748 ns)	-	max(3 nCK, 3.748 ns)	-	max(3 nCK, 3.748 ns)	-	max(3 nCK, 3.748 ns)	-	nCK
Mode Register Set command cycle time in CAL mode	tMRD_tCAL	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	nCK
Mode Register Set update delay in CAL mode	tMOD_tCAL	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	tMOD+tCAL	-	nCK
<b>DRAM Data Timing</b>																
DQS, DQS# to DQ skew, per group, per access	tDQSQ	-	0.20	-	0.19	-	0.18	-	0.17	-	0.16	-	0.16	-	0.16	tCK(avg)/2
DQ output hold time per group, per access from DQS, DQS#	tQH	0.70	-	0.72	-	0.74	-	0.74	-	0.76	-	0.76	-	0.76	-	tCK(avg)/2
Data Valid Window per device, per UI: (tQH - tDQSQ) of each UI on a given DRAM	tDVWd	0.64	-	0.64	-	0.64	-	0.64	-	0.64	-	0.63	-	0.63	-	UI
Data Valid Window, per pin, per UI: (tQH - tDQSQ) each UI on a pin of a given DRAM	tDVWp	0.72	-	0.72	-	0.72	-	0.72	-	0.69	-	0.66	-	0.66	-	UI
DQ low impedance time from CK, CK#	tLZ(DQ)	-250	160	-280	165	-310	170	-330	175	-360	180	-390	195	-450	225	ps
DQ high impedance time from CK, CK#	tHZ(DQ)	-	160	-	165	-	170	-	175	-	180	-	195	-	225	ps
<b>Data Strobe Timing</b>																
DQS, DQS# differential READ Pre-amble (1 clock preamble)	tRPRE	0.9	NOTE 1	0.9	NOTE 1	0.9	NOTE 1	0.9	NOTE 1	0.9	NOTE 1	0.9	NOTE 1	0.9	NOTE 1	tCK
DQS, DQS# differential READ Preamble (2 clock preamble)	tRPRE2	1.8	NOTE 1	1.8	NOTE 1	1.8	NOTE 1	1.8	NOTE 1	NA	NA	NA	NA	NA	NA	tCK
DQS, DQS# differential READ Postamble	tRPST	0.33	NOTE 2	0.33	NOTE 2	0.33	NOTE 2	0.33	NOTE 2	0.33	NOTE 2	0.33	NOTE 2	0.33	NOTE 2	tCK
DQS, DQS# differential output high time	tQSH	0.4	-	0.4	-	0.4	-	0.4	-	0.4	-	0.4	-	0.4	-	tCK
DQS, DQS# differential output low time	tQSL	0.4	-	0.4	-	0.4	-	0.4	-	0.4	-	0.4	-	0.4	-	tCK
DQS, DQS# differential WRITE Preamble (1 clock preamble)	tWPRE	0.9	-	0.9	-	0.9	-	0.9	-	0.9	-	0.9	-	0.9	-	tCK
DQS, DQS# differential WRITE Preamble (2 clock preamble)	tWPRE2	1.8	-	1.8	-	1.8	-	1.8	-	NA	NA	NA	NA	NA	NA	tCK
DQS, DQS# differential WRITE Postamble	tWPST	0.33	-	0.33	-	0.33	-	0.33	-	0.33	-	0.33	-	0.33	-	tCK
DQS and DQS# low-impedance time (Referenced from RL-1)	tLZ(DQS)	-250	160	-280	165	-310	170	-330	175	-360	180	-390	195	-450	225	ps
DQS and DQS# high-impedance time (Referenced from RL+BL/2)	tHZ(DQS)	-	160	-	165	-	170	-	175	-	180	-	195	-	225	ps
DQS, DQS# differential input low pulse width	tDQSL	0.46	0.54	0.46	0.54	0.46	0.54	0.46	0.54	0.46	0.54	0.46	0.54	0.46	0.54	tCK
DQS, DQS# differential input high pulse width	tDQSH	0.46	0.54	0.46	0.54	0.46	0.54	0.46	0.54	0.46	0.54	0.46	0.54	0.46	0.54	tCK
DQS, DQS# rising edge to CK, CK# rising edge (1 clock preamble)	tDQSS	-0.27	0.27	-0.27	0.27	-0.27	0.27	-0.27	0.27	-0.27	0.27	-0.27	0.27	-0.27	0.27	tCK
DQS, DQS# rising edge to CK, CK# rising edge (2 clock preamble)	tDQSS2	-0.5	0.5	-0.5	0.5	-0.5	0.5	-0.5	0.5	N/A	N/A	N/A	N/A	N/A	N/A	tCK
DQS, DQS# falling edge setup time to CK, CK# rising edge	tDSS	0.18	-	0.18	-	0.18	-	0.18	-	0.18	-	0.18	-	0.18	-	tCK
DQS, DQS# falling edge hold time from CK, CK# rising edge	tDSH	0.18	-	0.18	-	0.18	-	0.18	-	0.18	-	0.18	-	0.18	-	tCK
DQS, DQS# rising edge output timing location from rising CK, CK# with DLL On mode	tDQSCK (DLL On)	-160	160	-165	165	-170	170	-175	175	-180	180	-195	195	-225	225	ps
DQS, DQS# rising edge output variance window per DRAM	tDQSCKI (DLL On)	-	260	-	265	-	270	-	290	-	310	-	330	-	370	ps

# Product Specifications

PART NO.:

**VL41A4G63B-C3SA**
**REV: 1.0**

## AC TIMING PARAMETERS & SPECIFICATIONS

Speed		C3 DDR4-3200		C2 DDR4-2933		N8 DDR4-2666		N7 DDR4-2400		N6 DDR4-2133		M4 DDR4-1866		K2 DDR4-1600		Units
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
<b>MPSM Timing</b>																
Command path disable delay upon MPSM entry	tMPED	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	-
Valid clock requirement after MPSM entry	tCKMPE	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	$t_{MOD(min)} + t_{CP-DED(min)}$	-	-
Valid clock requirement before MPSM exit	tCKMPX	$\leq SRX(mi\ n)$	-	$\leq SRX(mi\ n)$	-	$\leq SRX(mi\ n)$	-	$\leq SRX(mi\ n)$	-	$\leq SRX(mi\ n)$	-	$\leq SRX(mi\ n)$	-	$\leq SRX(mi\ n)$	-	-
Exit MPSM to commands not requiring a locked DLL	tXMP	$t_{XS(min)}$	-	$t_{XS(min)}$	-	$t_{XS(min)}$	-	$t_{XS(min)}$	-	$t_{XS(min)}$	-	$t_{XS(min)}$	-	$t_{XS(min)}$	-	-
Exit MPSM to commands requiring a locked DLL	tXMPDLL	$t_{XMP(min)} + t_{XS-DLL(min)}$	-	$t_{XMP(min)} + t_{XS-DLL(min)}$	-	$t_{XMP(min)} + t_{XS-DLL(min)}$	-	$t_{XMP(min)} + t_{XS-DLL(min)}$	-	$t_{XMP(min)} + t_{XS-DLL(min)}$	-	$t_{XMP(min)} + t_{XS-DLL(min)}$	-	$t_{XMP(min)} + t_{XS-DLL(min)}$	-	-
CS setup time to CKE	tMPX_S	$t_{IS(min)} + t$	-	$t_{IS(min)} + t$	-	$t_{IS(min)} + t$	-	$t_{IS(min)} + t$	-	$t_{IS(min)} + t$	-	$t_{IS(min)} + t$	-	$t_{IS(min)} + t$	-	-
CS# High hold time to CKE rising edge	tMPX_HH	$t_{XP(min)}$	-	$t_{XP(min)}$	-	$t_{XP(min)}$	-	$t_{XP(min)}$	-	$t_{XP(min)}$	-	$t_{XP(min)}$	-	$t_{XP(min)}$	-	-
CS# Low hold time to CKE rising edge	tMPX_LH	12	$t_{XMP}^-$ 10ns	12	$t_{XMP}^-$ 10ns	12	$t_{XMP}^-$ 10ns	12	$t_{XMP}^-$ 10ns	12	$t_{XMP}^-$ 10ns	12	$t_{XMP}^-$ 10ns	12	$t_{XMP}^-$ 10ns	ns
<b>Calibration Timing</b>																
Power-up and RESET calibration time	tZQinit	1024	-	1024	-	1024	-	1024	-	1024	-	1024	-	1024	-	nCK
Normal operation Full calibration time	tZQoper	512	-	512	-	512	-	512	-	512	-	512	-	512	-	nCK
Normal operation Short calibration time	tZQCS	128	-	128	-	128	-	128	-	128	-	128	-	128	-	nCK
<b>Reset/Self Refresh Timing</b>																
Exit Reset from CKE HIGH to a valid command	tXPR	max (5nCK, 1R FC(min))+ 10ns	-	max (5nCK, 1R FC(min))+ 10ns	-	max (5nCK, 1R FC(min))+ 10ns	-	max (5nCK, 1R FC(min))+ 10ns	-	max (5nCK, 1R FC(min))+ 10ns	-	max (5nCK, 1R FC(min))+ 10ns	-	max (5nCK, 1R FC(min))+ 10ns	-	nCK
Exit Self Refresh to commands not requiring a locked DLL	tXS	$t_{RFC(min)} + 10ns$	-	$t_{RFC(min)} + 10ns$	-	$t_{RFC(min)} + 10ns$	-	$t_{RFC(min)} + 10ns$	-	$t_{RFC(min)} + 10ns$	-	$t_{RFC(min)} + 10ns$	-	$t_{RFC(min)} + 10ns$	-	nCK
SRX to commands not requiring a locked DLL in Self Refresh ABORT	tX-S_ABORT(min)	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	nCK
Exit Self Refresh to ZQCL, ZQCS and MRS (CL, CWL, WR, RTP and Gear Down)	tXS_FAST(min)	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	$t_{RFC4(mi\ n)} + 10ns$	-	nCK
Exit Self Refresh to commands requiring a locked DLL	tXSDLL	LLK(mi n)	-	LLK(mi n)	-	LLK(mi n)	-	LLK(mi n)	-	LLK(mi n)	-	LLK(mi n)	-	LLK(mi n)	-	nCK
Minimum CKE low width for Self refresh entry to exit timing	tCKESR	$t_{CKE(min)} + 1nCK$	-	$t_{CKE(min)} + 1nCK$	-	$t_{CKE(min)} + 1nCK$	-	$t_{CKE(min)} + 1nCK$	-	$t_{CKE(min)} + 1nCK$	-	$t_{CKE(min)} + 1nCK$	-	$t_{CKE(min)} + 1nCK$	-	nCK
Minimum CKE low width for Self refresh entry to exit timing with CA Parity enabled	tCKESR_PAR	$t_{CKE(min)} + 1nCK + PL$	-	$t_{CKE(min)} + 1nCK + PL$	-	$t_{CKE(min)} + 1nCK + PL$	-	$t_{CKE(min)} + 1nCK + PL$	-	$t_{CKE(min)} + 1nCK + PL$	-	$t_{CKE(min)} + 1nCK + PL$	-	$t_{CKE(min)} + 1nCK + PL$	-	nCK
Valid Clock Requirement after Self Refresh Entry (SRE) or Power-Down Entry (PDE)	tCKSRE	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	nCK
Valid Clock Requirement after Self Refresh Entry (SRE) or Power-Down when CA Parity is enabled	tCKS-RE_PA R	max (5nCK, 10 ns)+ PL	-	max (5nCK, 10 ns)+ PL	-	max (5nCK, 10 ns)+ PL	-	max (5nCK, 10 ns)+ PL	-	max (5nCK, 10 ns)+ PL	-	max (5nCK, 10 ns)+ PL	-	max (5nCK, 10 ns)+ PL	-	nCK
Valid Clock Requirement before Self Refresh Exit (SRX) or Power-Down Exit (PDX) or Reset Exit	tCKSRX	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	max (5nCK, 10 ns)	-	nCK
<b>Power Down Timing</b>																
Exit Power Down with DLL on to any valid command; Exit Pre-charge Power Down with DLL frozen to commands not requiring a locked DLL	tXP	max (4nCK, 6ns)	-	max (4nCK, 6ns)	-	max (4nCK, 6ns)	-	max (4nCK, 6ns)	-	max (4nCK, 6ns)	-	max (4nCK, 6ns)	-	max (4nCK, 6ns)	-	nCK
CKE minimum pulse width	tCKE	max (3nCK, 5ns)	-	max (3nCK, 5ns)	-	max (3nCK, 5ns)	-	max (3nCK, 5ns)	-	max (3nCK, 5ns)	-	max (3nCK, 5ns)	-	max (3nCK, 5ns)	-	nCK
Command pass disable delay	tCPDED	4	-	4	-	4	-	4	-	4	-	4	-	4	-	nCK

# Product Specifications

**PART NO.:**
**VL41A4G63B-C3SA**
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## AC TIMING PARAMETERS & SPECIFICATIONS

Speed		C3 DDR4-3200		C2 DDR4-2933		N8 DDR4-2666		N7 DDR4-2400		N6 DDR4-2133		M4 DDR4-1866		K2 DDR4-1600		Units
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
Power Down Entry to Exit Timing	tPD	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	nCK
Timing of ACT command to Power Down entry	tACTPDEN	2	-	2	-	2	-	2	-	2	-	1	-	1	-	nCK
Timing of PRE or PREA command to Power Down entry	tPRPDEN	2	-	2	-	2	-	2	-	2	-	1	-	1	-	nCK
Timing of RD/RDA command to Power Down entry	tRDPDEN	RL+4+1	-	RL+4+1	-	RL+4+1	-	RL+4+1	-	RL+4+1	-	RL+4+1	-	RL+4+1	-	nCK
Timing of WR command to Power Down entry (BL8OTF, BL8MRS, BC4OTF)	tWRPDEN	WL+4+(tWR/tCK(avg))	-	WL+4+(tWR/tCK(avg))	-	WL+4+(tWR/tCK(avg))	-	WL+4+(tWR/tCK(avg))	-	WL+4+(tWR/tCK(avg))	-	WL+4+(tWR/tCK(avg))	-	WL+4+(tWR/tCK(avg))	-	nCK
Timing of WRA command to Power Down entry (BL8OTF, BL8MRS, BC4OTF)	tWRAPDEN	WL+4+W R+1	-	WL+4+W R+1	-	WL+4+W R+1	-	WL+4+W R+1	-	WL+4+W R+1	-	WL+4+W R+1	-	WL+4+W R+1	-	nCK
Timing of WR command to Power Down entry (BC4MRS)	tWRP-BC4DEN	WL+2+(tWR/tCK(avg))	-	WL+2+(tWR/tCK(avg))	-	WL+2+(tWR/tCK(avg))	-	WL+2+(tWR/tCK(avg))	-	WL+2+(tWR/tCK(avg))	-	WL+2+(tWR/tCK(avg))	-	WL+2+(tWR/tCK(avg))	-	nCK
Timing of WRA command to Power Down entry (BC4MRS)	tWRAP-BC4DEN	WL+2+W R+1	-	WL+2+W R+1	-	WL+2+W R+1	-	WL+2+W R+1	-	WL+2+W R+1	-	WL+2+W R+1	-	WL+2+W R+1	-	nCK
Timing of REF command to Power Down entry	tREFPDEN	2	-	2	-	2	-	2	-	2	-	1	-	1	-	nCK
Timing of MRS command to Power Down entry	tMRSPDEN	OD(mi n)	-	OD(mi n)	-	OD(mi n)	-	OD(mi n)	-	OD(mi n)	-	OD(mi n)	-	OD(mi n)	-	
<b>PDA Timing</b>																
Mode Register Set command cycle time in PDA mode	tMRD_PDA	max(16n CK, 10ns)	-	max(16n CK, 10ns)	-	max(16n CK, 10ns)	-	max(16n CK, 10ns)	-	max(16n CK, 10ns)	-	max(16n CK, 10ns)	-	max(16n CK, 10ns)	-	nCK
Mode Register Set command update delay in PDA mode	tMOD_PDA	tMOD		tMOD		tMOD		tMOD		tMOD		tMOD		tMOD		
<b>ODT Timing</b>																
Asynchronous RTT turn-on delay (Power-Down with DLL frozen)	tAONAS	1.0	9.0	1.0	9.0	1.0	9.0	1.0	9.0	1.0	9.0	1.0	9.0	1.0	9.0	ns
Asynchronous RTT turn-off delay (Power-Down with DLL frozen)	tAOFAS	1.0	9.0	1.0	9.0	1.0	9.0	1.0	9.0	1.0	9.0	1.0	9.0	1.0	9.0	ns
RTT dynamic change skew	tADC	0.26	0.74	0.26	0.74	0.28	0.72	0.3	0.7	0.3	0.7	0.3	0.7	0.3	0.7	tCK(avg)
<b>Write Leveling Timing</b>																
First DQS/DQS# rising edge after write leveling mode is programmed	tWLMRD	40	-	40	-	40	-	40	-	40	-	40	-	40	-	nCK
DQS/DQS# delay after write leveling mode is programmed	tWLDQSEN	25	-	25	-	25	-	25	-	25	-	25	-	25	-	nCK
Write leveling setup time from rising CK, CK# crossing to rising DQS/DQS# crossing	tWLS	0.13	-	0.13	-	0.13	-	0.13	-	0.13	-	0.13	-	0.13	-	tCK(avg)
Write leveling hold time from rising DQS/DQS# crossing to rising CK, CK# crossing	tWLH	0.13	-	0.13	-	0.13	-	0.13	-	0.13	-	0.13	-	0.13	-	tCK(avg)
Write leveling output delay	tWLO	0	9.5	0	9.5	0	9.5	0	9.5	0	9.5	0	9.5	0	9.5	ns
Write leveling output error	tWLOE	0	2	0	2	0	2	0	2	0	2	0	2	0	2	ns
<b>CA Parity Timing</b>																
Commands not guaranteed to be executed during this time	tPAR_UN - KNOWN	-	PL	-	PL	-	PL	-	PL	-	PL	-	PL	-	PL	
Delay from errant command to ALERT# assertion	tPAR_ALERT_ON	-	PL+6ns	-	PL+6ns	-	PL+6ns	-	PL+6ns	-	PL+6ns	-	PL+6ns	-	PL+6ns	
Pulse width of ALERT# signal when asserted	tPAR_ALERT_PW	96	192	88	176	80	160	72	144	64	128	56	112	48	96	nCK
Time from when Alert is asserted till controller must start providing DES commands in Persistent CA parity mode	tPAR_ALERT_RSP	-	85	-	78	-	71	-	64	-	57	-	50	-	43	nCK
Parity Latency	PL	6		6		5		5		4		4		4		nCK
<b>CRC Error Reporting</b>																
CRC error to ALERT# latency	tCRC_ALERT	3	13	3	13	3	13	3	13	3	13	3	13	3	13	ns
CRC ALERT# pulse width	tCRC_ALERT_PW	6	10	6	10	6	10	6	10	6	10	6	10	6	10	nCK

# Product Specifications

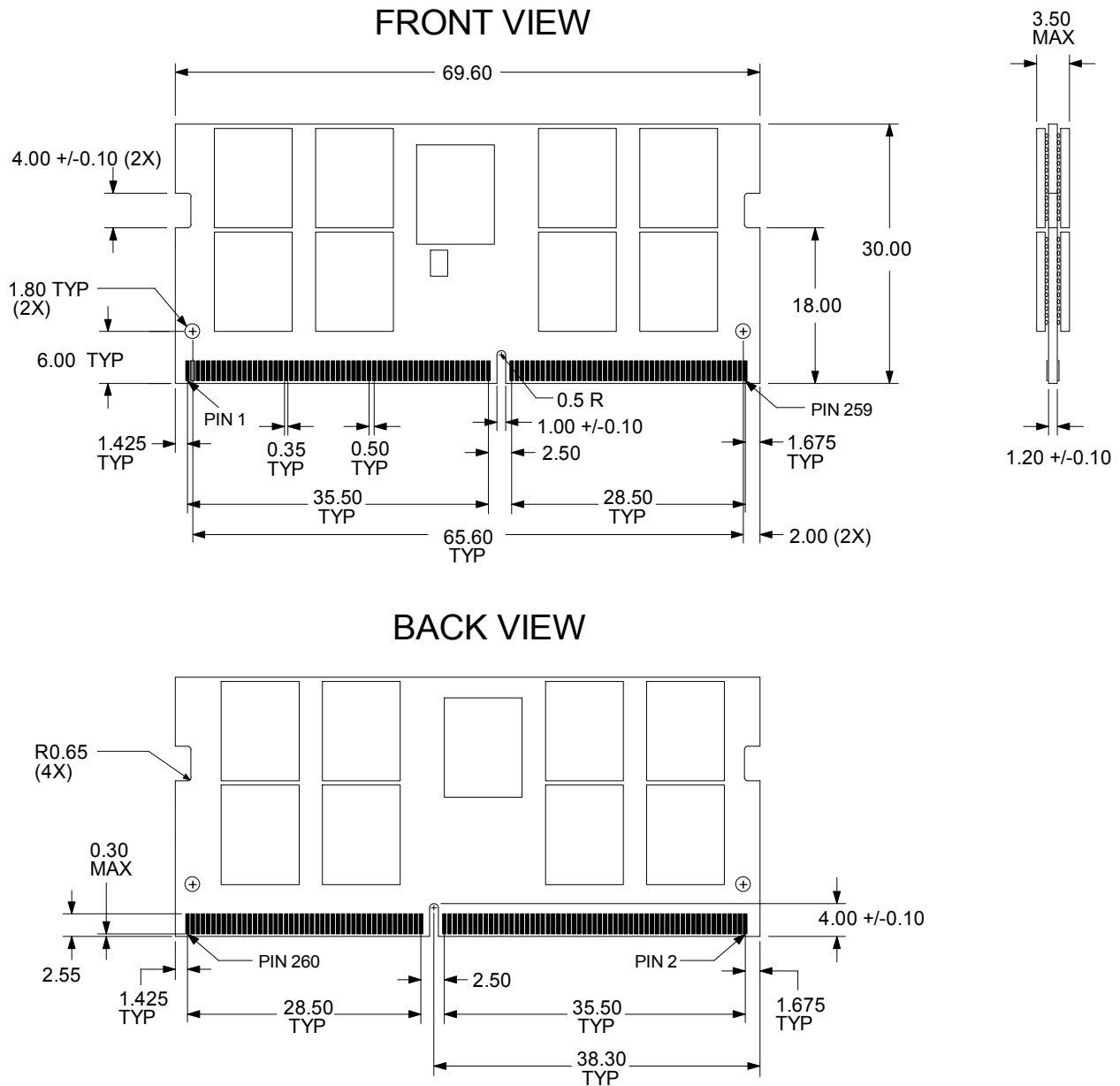
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## AC TIMING PARAMETERS & SPECIFICATIONS

Speed		C3 DDR4-3200		C2 DDR4-2933		N8 DDR4-2666		N7 DDR4-2400		N6 DDR4-2133		M4 DDR4-1866		K2 DDR4-1600		Units
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
<b>Geardown timing</b>																
Exit RESET from CKE HIGH to a valid MRS geardown (T2/Reset)	tX-PR_GEAR	tXPR	-	tXPR	-	tXPR	-	-	-	-	-	-	-	-	-	
CKE High Assert to Gear Down Enable time(T2/CKE)	tXS_GEAR	tXS	-	tXS	-	tXS	-	-	-	-	-	-	-	-	-	
MRS command to Sync pulse time(T3)	tSYN-C_GEAR	tMOD + 4tCK	-	tMOD + 4tCK	-	tMOD + 4tCK	-	-	-	-	-	-	-	-	-	
Sync pulse to First valid command(T4)	tCM-D_GEAR	tMOD	-	tMOD	-	tMOD	-	-	-	-	-	-	-	-	-	
Geardown setup time	tGEAR_setup	2	-	2	-	2	-	-	-	-	-	-	-	-	-	nCK
Geardown hold time	tGEAR_hold	2	-	2	-	2	-	-	-	-	-	-	-	-	-	nCK
<b>tREFI</b>																
tRFC1 (min) 550ns setting (NOTE 3,4)	2Gb	160	-	160	-	160	-	160	-	160	-	160	-	160	-	ns
	4Gb	260	-	260	-	260	-	260	-	260	-	260	-	260	-	ns
	8Gb	350	-	350	-	350	-	350	-	350	-	350	-	350	-	ns
	16Gb	550	-	550	-	550	-	550	-	550	-	550	-	550	-	ns
tRFC1 (min)_350ns setting	16Gb	350	-	350	-	350	-	350	-	350	-	350	-	350	-	ns
tRFC2 (min) 550ns setting (NOTE 3,4)	2Gb	110	-	110	-	110	-	110	-	110	-	110	-	110	-	ns
	4Gb	160	-	160	-	160	-	160	-	160	-	160	-	160	-	ns
	8Gb	260	-	260	-	260	-	260	-	260	-	260	-	260	-	ns
	16Gb	350	-	350	-	350	-	350	-	350	-	350	-	350	-	ns
tRFC2 (min)_350ns setting	16Gb	260	-	260	-	260	-	260	-	260	-	260	-	260	-	ns
tRFC4 (min) 550ns setting (NOTE 3,4)	2Gb	90	-	90	-	90	-	90	-	90	-	90	-	90	-	ns
	4Gb	110	-	110	-	110	-	110	-	110	-	110	-	110	-	ns
	8Gb	160	-	160	-	160	-	160	-	160	-	160	-	160	-	ns
	16Gb	260	-	260	-	260	-	260	-	260	-	260	-	260	-	ns
tRFC4 (min)_350ns setting	16Gb	160	-	160	-	160	-	160	-	160	-	160	-	160	-	ns
Note: <ol style="list-style-type: none"> <li>1. The maximum read preamble is bounded by tLZ(DQS)min on the left side and tDQSCK(max) on the right side. Boundary of DQS Low-Z occur one cycle earlier in 2tCK toggle mode.</li> <li>2. DQ falling signal middle-point of transferring from High to Low to first rising edge of DQS diff-signal cross-point.</li> <li>3. Parameters apply from tCK(avg)min to tCK(avg)max at all standard JEDEC clock period values as stated in the Speed Bin Tables.</li> <li>4. 16Gb A-die 2Gx8 product supports both tRFC1 550ns and 350ns setting. It depends on customer's preference. tRFC2 and tRFC4 needs to be set corresponding to each setting values.</li> </ol>																

Product Specifications		
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## Package Dimensions



Notes: 1. All dimensions are in millimeters with tolerance +/- 0.15mm unless otherwise specified.  
 2. The dimensional diagram is for reference only.